

General Description

The CMSC3811 is the highest performance trench N-ch and P-ch MOSFETs with high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

Features

- 30V, 20A, $R_{DS(ON)} = 8.5\text{m}\Omega$ @ $V_{GS} = 10\text{V}$
-30V, -15A, $R_{DS(ON)} = 35\text{m}\Omega$ @ $V_{GS} = -10\text{V}$
- Improved dv/dt capability
- Fast switching
- RoHS Compliant

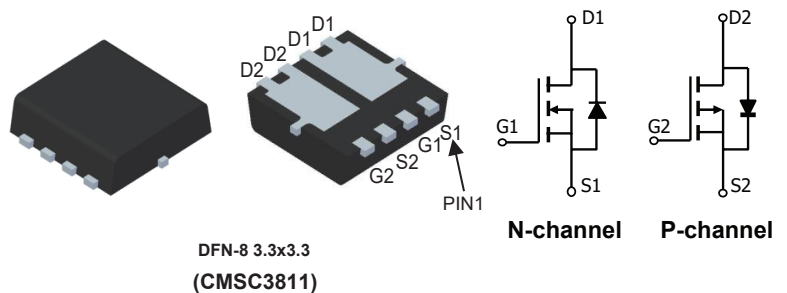
Product Summary

	BVDSS	$R_{DS(on)}$ max.	ID
N-Channel	30V	8.5m Ω	20A
P-Channel	-30V	35m Ω	-15A

Applications

- Synchronous Rectification.
- High Current, High Speed Switching.
- Portable equipment application

DFN-8 3.3x3.3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Max N-channel	Max P-channel	Units
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current	20	-15	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current	13	-10	A
I_{DM}	Pulsed Drain Current	60	-45	A
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	10	10	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ\text{C}$

Thermal Characteristics: N-channel

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Maximum Junction-to-Ambient (Steady-State)	---	61	$^\circ\text{C/W}$
$R_{\theta JC}$	Maximum Junction-to-Case (Steady-State)	---	7.5	$^\circ\text{C/W}$

Thermal Characteristics: P-channel

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Maximum Junction-to-Ambient (Steady-State)	---	70	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Maximum Junction-to-Case (Steady-State)	---	8	$^{\circ}\text{C}/\text{W}$

N-channel Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=15\text{A}$	---	---	8.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=15\text{A}$	---	---	13	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu\text{A}$	1	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$	---	---	1	μA
		$V_{DS}=20\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^{\circ}\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=10\text{A}$	---	8	---	S
Q_g	Total Gate Charge	$V_{DS}=20\text{V}$, $I_D=6\text{A}$ $V_{GS}=4.5\text{V}$	---	2.7	---	nC
Q_{gs}	Gate-Source Charge		---	1.5	---	
Q_{gd}	Gate-Drain Charge		---	1.7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=12\text{V}$, $V_{GS}=10\text{V}$, $R_G=3.3\Omega$ $I_D=5\text{A}$	---	5	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	12	---	
T_f	Fall Time		---	2.5	---	
C_{iss}	Input Capacitance	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	1000	---	pF
C_{oss}	Output Capacitance		---	40	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0\text{V}$, Force Current	---	---	20	A
$I_{S,pulse}$	Diode pulse current		---	---	60	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_F=1\text{A}$, $T_J=25^{\circ}\text{C}$	---	---	1	V

P Channel Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-30	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-10A	---	---	35	mΩ
		V _{GS} =-4.5V, I _D =-10A	---	---	43	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250μA	-1	---	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	---	---	-1	uA
		V _{DS} =-20V, V _{GS} =0V	---	---	-10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-10A	---	9	---	S
Q _g	Total Gate Charge	V _{DS} =-20V, V _{GS} =-4.5V, I _D =-6A	---	6	---	nC
Q _{gs}	Gate-Source Charge		---	2	---	
Q _{gd}	Gate-Drain Charge		---	3.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-12V, V _{GS} =-10V, I _D =-5A R _G =3.3Ω	---	8.5	---	ns
T _r	Rise Time		---	10	---	
T _{d(off)}	Turn-Off Delay Time		---	22	---	
T _f	Fall Time		---	10	---	
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	1300	---	pF
C _{oss}	Output Capacitance		---	140	---	
C _{rss}	Reverse Transfer Capacitance		---	95	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-15	A
I _{SM}	Pulsed Source Current		---	---	-45	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _F =-1A, T _J =25°C	---	---	-1	V

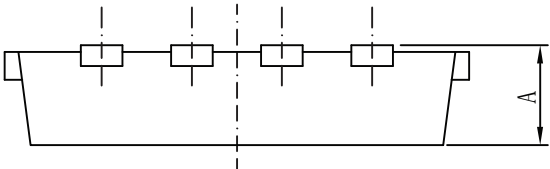
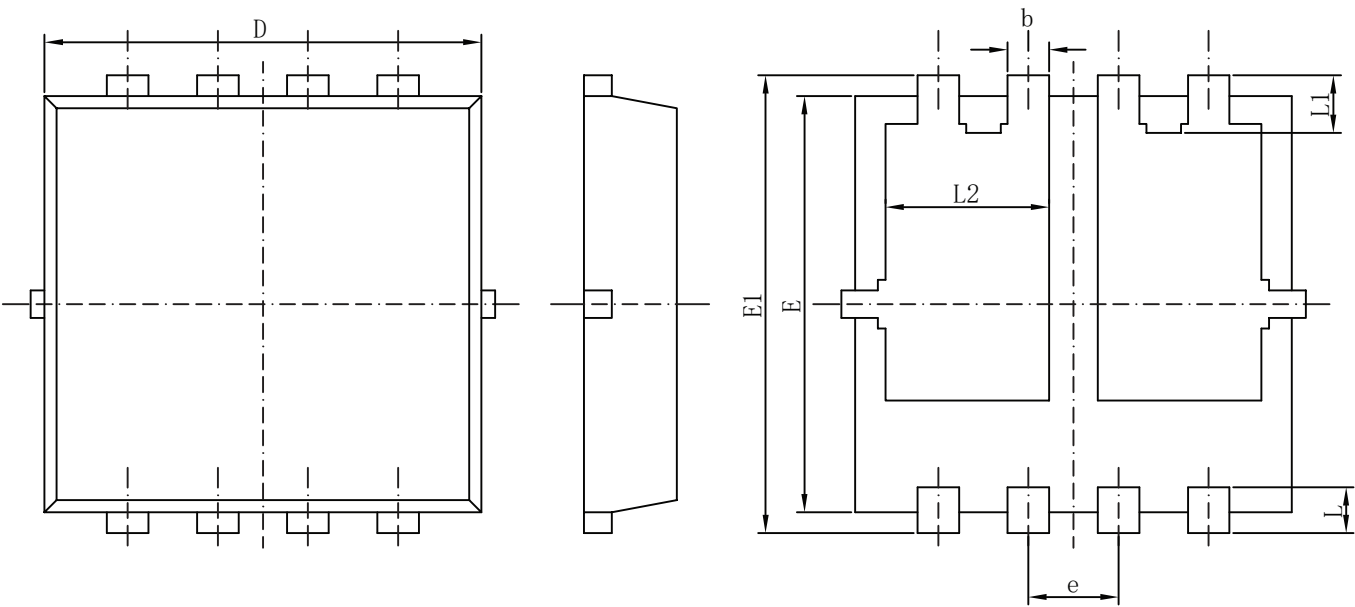
This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design, functions and reliability without notice. Please refer to the latest version of specification.

Package Dimension

DFN-8 3.3x3.3 Unit :mm



- 注：
1. 未注公差 ± 0.10
 2. 塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
 3. 标注单位mm

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.700	0.900	0.800
D	3.000	3.200	3.100
E	3.000	3.200	3.100
E1	3.200	3.600	3.400
b	0.200	0.400	0.300
e	0.550	0.750	0.650
L	0.300	0.600	0.450
L1	0.395	0.695	0.545
L2	0.885	1.185	1.035